

General Description

The HSBA6119 is the high cell density SGT P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications. The HSBA6119 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

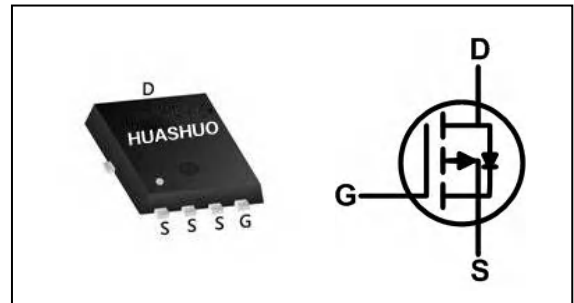
Features

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density SGT MOS Technology

Product Summary

V_{DS}	-60	V
$R_{DS(ON),typ}$	6	m Ω
I_D	-80	A

PRPAK5*6 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $-V_{GS} @ -10V^1$	-80	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $-V_{GS} @ -10V^1$	-45	A
I_{DM}	Pulsed Drain Current ²	-320	A
EAS	Single Pulse Avalanche Energy ³	400	mJ
I_{AS}	Avalanche Current	108	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	150	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.88	$^\circ\text{C/W}$



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-20A$	---	6	7.5	$m\Omega$
		$V_{GS}=-4.5V, I_D=-10A$	---	8	10	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	-2.0	-2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-60V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=-60V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	10	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	2	---	Ω
g_{fs}	Forward Transconductance	$V_{DS}=-10V, I_D=-10A$	---	30	---	S
Q_g	Total Gate Charge	$V_{DS}=-30V, V_{GS}=-10V, I_D=-15A$	---	55	---	nC
Q_{gs}	Gate-Source Charge		---	12	---	
Q_{gd}	Gate-Drain Charge		---	9	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-30V, V_{GS}=-10V, R_G=3\Omega, I_D=-15A$	---	4.5	---	ns
T_r	Rise Time		---	2.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	15	---	
T_f	Fall Time		---	4	---	
C_{iss}	Input Capacitance	$V_{DS}=-30V, V_{GS}=0V, f=1\text{MHz}$	---	3065	---	pF
C_{oss}	Output Capacitance		---	624	---	
C_{rss}	Reverse Transfer Capacitance		---	29	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-80	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	-320	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1	V
t_{rr}	Reverse Recovery Time	$I_F=-15A, di/dt=-100A/\mu s$, $T_J=25^\circ\text{C}$	---	58	---	nS
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	103	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-30V, V_{GS}=-10V, L=0.5mH, R_g=25\Omega, I_{AS}=-108A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

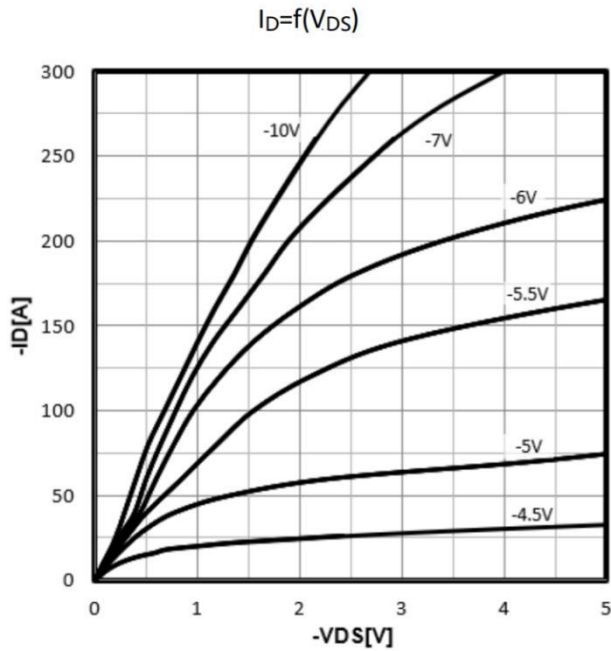


Fig.1 Typ. output characteristics

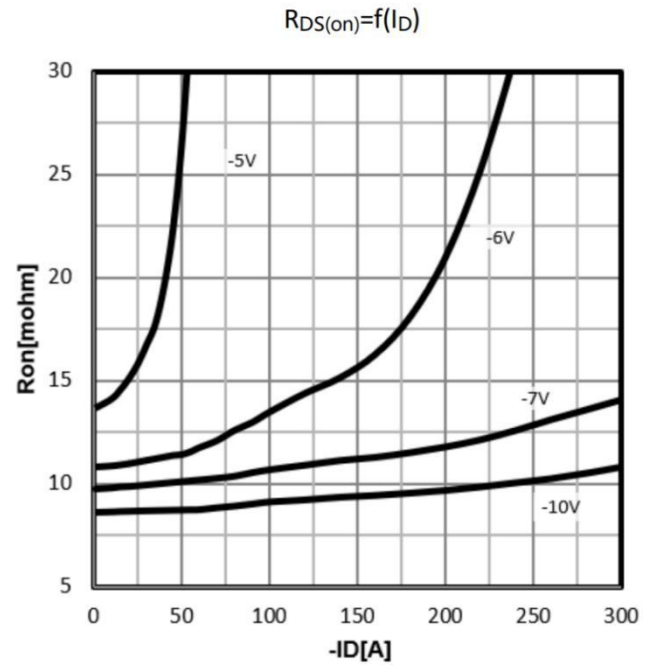


Fig.2 Typ. drain-source on

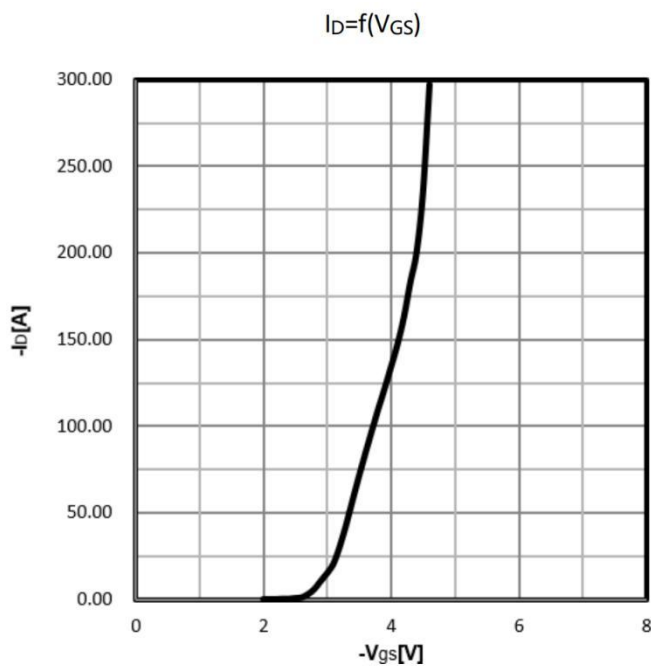


Fig.3 Typ. transfer characteristics

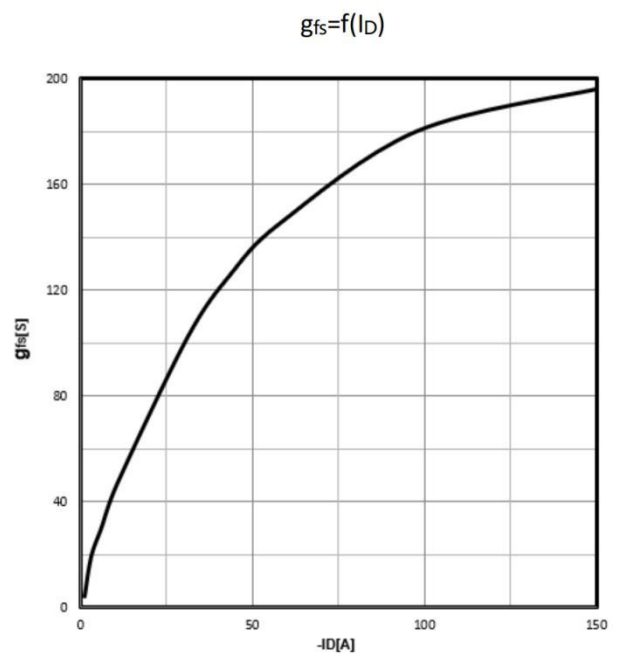


Fig.4 Typ. forward

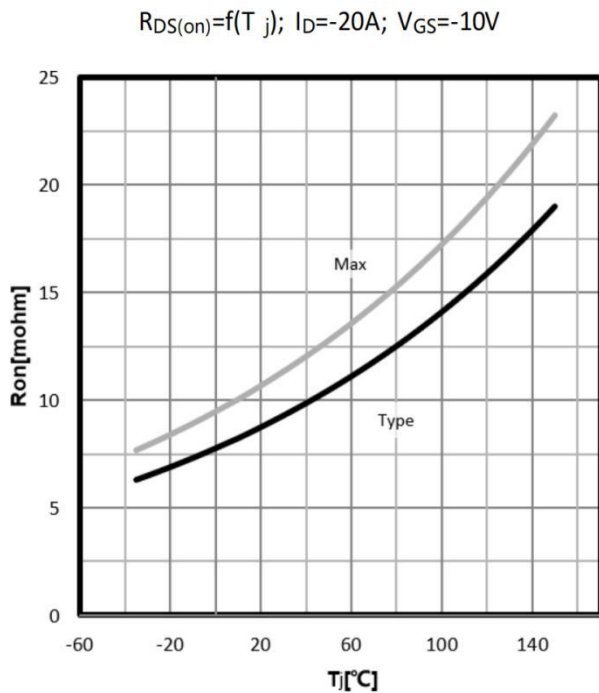


Fig.5 Drain-source on-state resistance

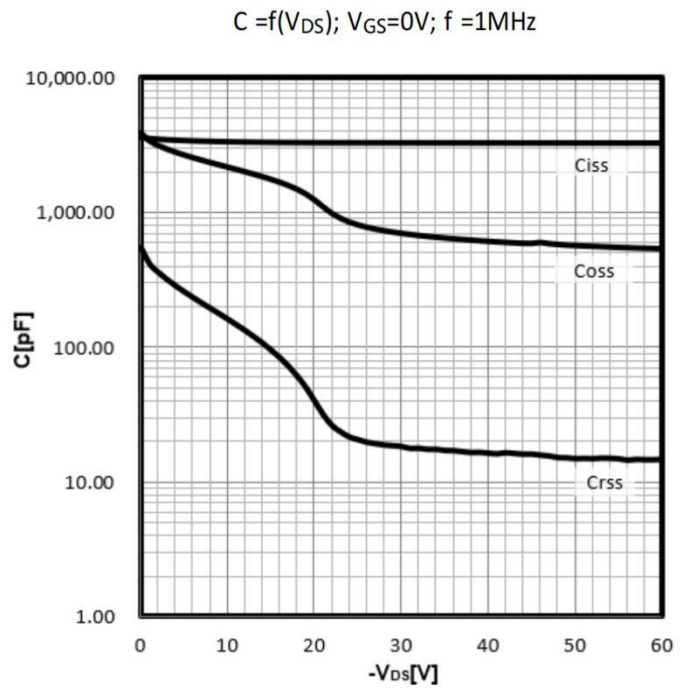


Fig.6 Typ. capacitances

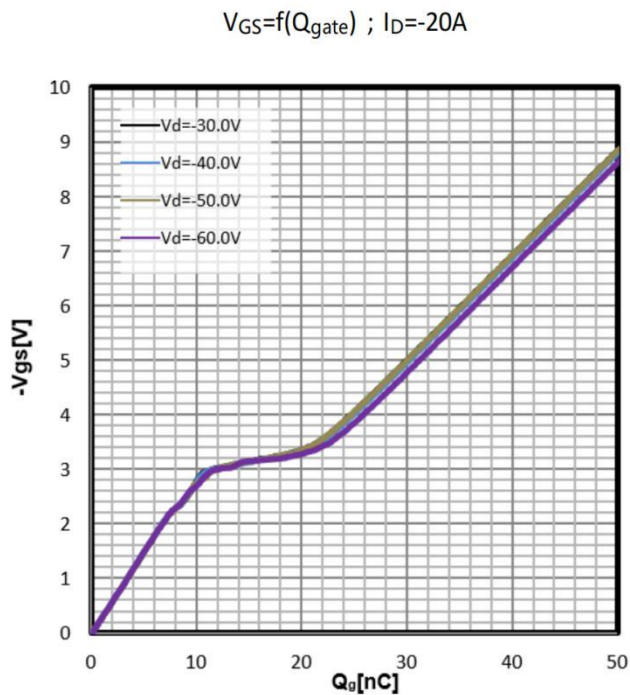


Fig.7 Typ. gate charge

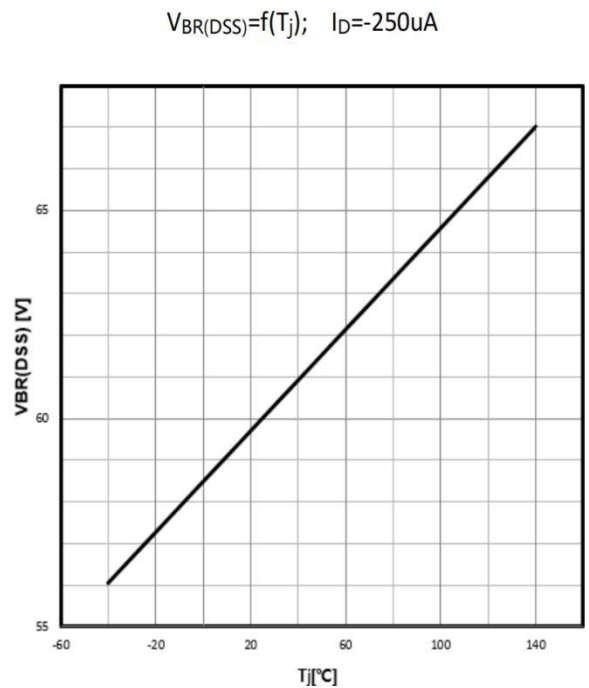


Fig.8 Drain-source breakdown voltage

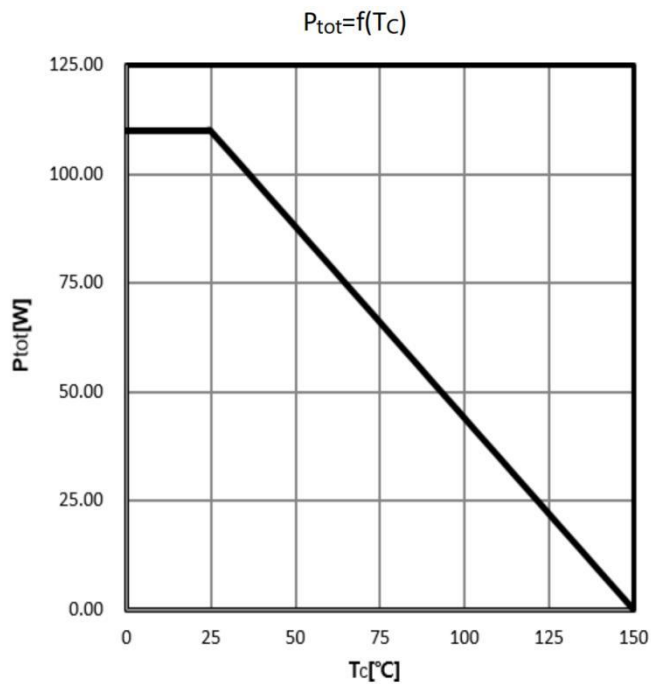


Fig.9 Power Dissipation

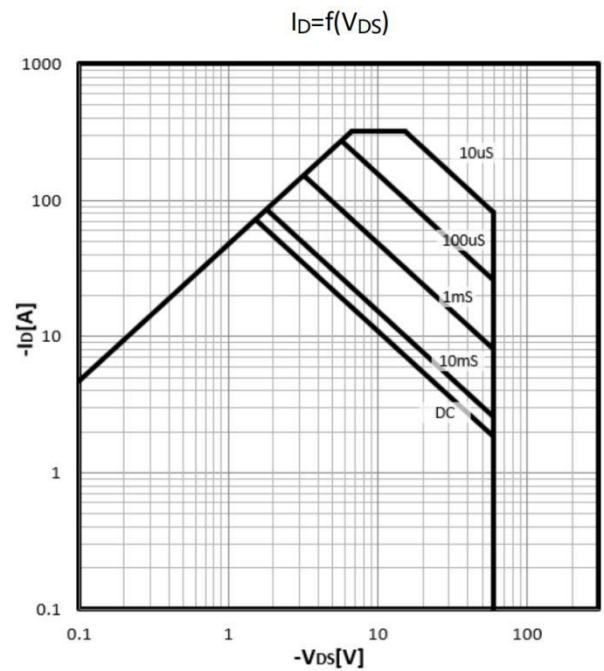


Fig.10 Safe operating area

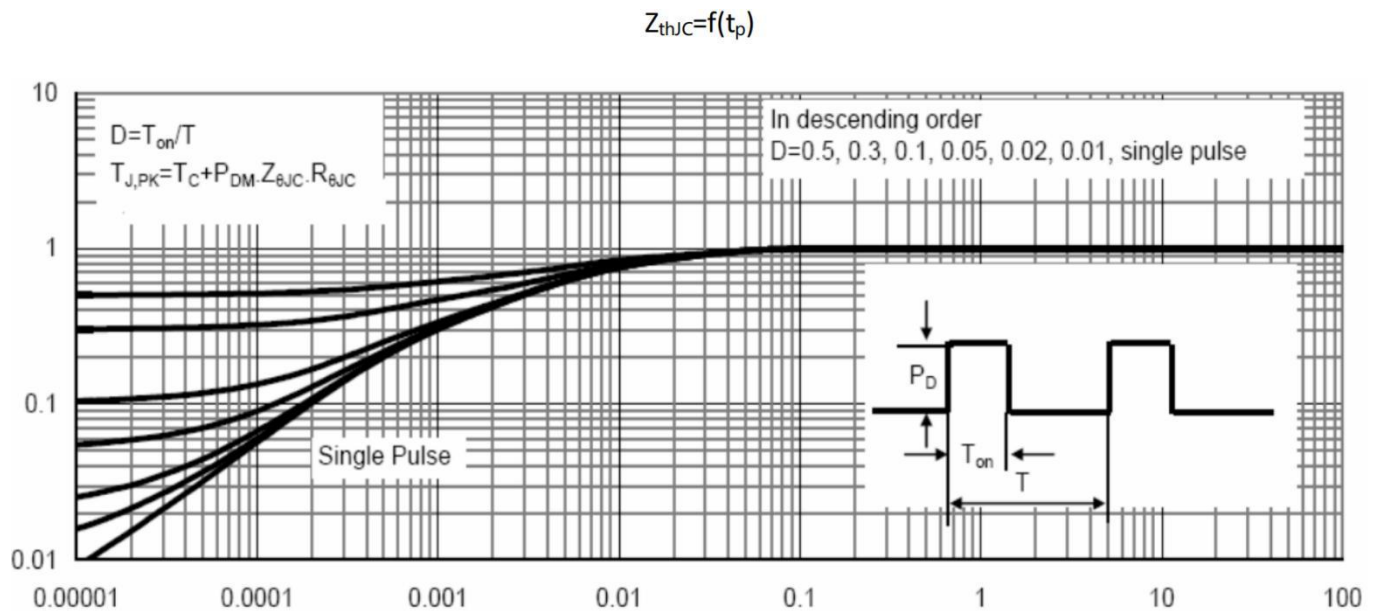
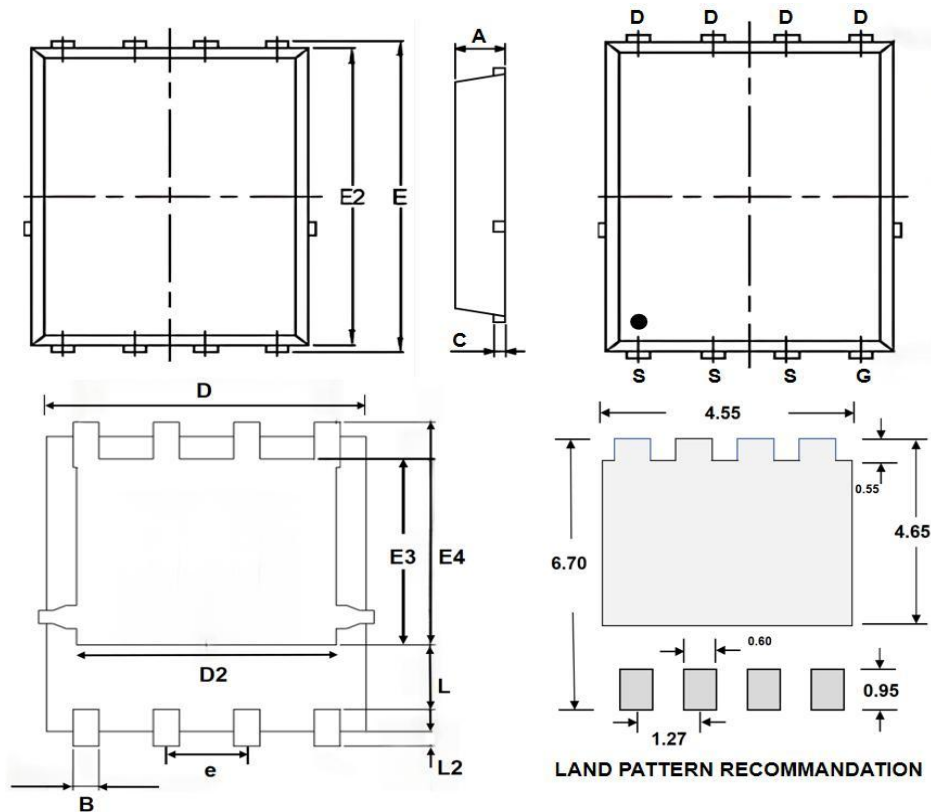


Fig.11 Max. transient thermal impedance

Ordering Information

Part Number	Package code	Packaging
HSBA6119	PRPAK5*6	3000/Tape&Reel

PRPAK5*6 Package Outline



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	--	1.20	0.031	--	0.047
B	0.25	--	0.51	0.012	--	0.020
C	0.15	--	0.35	0.006	--	0.014
D	4.80	--	5.45	0.189	--	0.209
D2	3.61	--	4.35	0.142	--	0.171
E	5.90	--	6.35	0.232	--	0.250
E2	5.42	--	6.06	0.213	--	0.232
E3	3.23	--	3.90	0.127	--	0.154
E4	3.69	--	4.55	0.145	--	0.179
L	0.61	--	1.80	0.024	--	0.071
L2	0.05	--	0.36	0.002	--	0.014
e	--	1.27	--	--	0.050	--

HSBA6119 Marking:

